

Approval Sheet

Customer	
Product Number	M0SB-56PB6C03-J
Module speed	PC-133
Pin	144 Pin
CAS Latency	CL-3
SDRAM Operating Temp.	0 °C ~ 70 °C
Date	2 nd November 2023

**The Total Solution For
Industrial Flash Storage**

Rev 1.1

1. Features

Key Parameter

Industry Nomenclature	Speed Grade	Data Rate MT/s			tRCD	tRP	tRC
		CL=2	CL=2.5	CL=3	(ns)	(ns)	(ns)
PC-133	B	100	-	133	20	20	65

- Single Pulsed RAS- interface
- Fully Synchronous to positive CLK edge
- 4 banks controlled by BA0 & BA1
- Multiple Burst Read with single write option
- Automatic and controlled precharge command
- Auto refresh (CBR) and Self-Refresh
- Standard 144-pin Memory Module
- Intend for 133 MHz applications
- Inputs and Outputs are LVTTTL compatible
- VDD=VDDQ= 3.3 Volt $\pm$ 0.3
- Serial Presence Detect with EEPROM
- SDRAM Operation Temperature (*Note 1*)
 - $0^{\circ}\text{C} \leq T_A \leq +70^{\circ}\text{C}$
- Programmable Device Operation:
 - Burst Type: Sequential or Interleave
 - Device CAS# Latency:2, 3
- RoHS Compliant (*Section 14*)

Note:1. The refresh rate is required to double when T_A Exceeds 70°C .

2. SDRAM Environmental Requirements

iDIMM's SDRAMs are intended for use in standard office environments that have limited capacity for heating and air conditioning.

Symbol	Parameter	Rating	Units	Notes
T _{OPR}	Operating Temperature (ambient)	0 to +70	°C	1
T _{STG}	Storage Temperature	-55 to +150	°C	
1. The refresh rate is required to double when T _c exceeds 85°C.				

3. Ordering Information

SDR SODIMM						
Part Number	Density	Speed	Organization	Number of DRAM	Number of rank	ECC
M0SB-56PB6C03-J	256MB	PC-133	32Mx16	4	1	N

Pin Configurations (Front side/Back side)

Pin	Front	Pin	Back	Pin	Front	Pin	Back	Pin	Front	Pin	Back
1	V _{SS}	2	V _{SS}	51	DQM14	52	DQM46	95	DQ21	96	DQ53
3	DQ0	4	DQ32	53	DQM15	54	DQM47	97	DQ22	98	DQ54
5	DQ1	6	DQ33	55	V _{SS}	56	V _{SS}	99	DQ23	100	DQ55
7	DQ2	8	DQ34	57	NC	58	NC	101	V _{DD}	102	V _{DD}
9	DQ3	10	DQ35	59	NC	60	NC	103	A6	104	A7
11	V _{DD}	12	V _{DD}	Voltage Key				105	A8	106	BA0
13	DQ4	14	DQ36					107	V _{SS}	108	V _{SS}
15	DQ5	16	DQ37					109	A9	110	BA1
17	DQ6	18	DQ38					111	A10/AP	112	A11
19	DQ7	20	DQ39	61	**CLK0	62	**CKE0	113	V _{DD}	114	V _{DD}
21	V _{SS}	22	V _{SS}	63	V _{DD}	64	V _{DD}	115	DQM2	116	DQM6
23	DQM0	24	DQM4	65	RAS	66	CAS	117	DQM3	118	DQM7
25	DQM1	26	DQM5	67	WE	68	**CKE1	119	V _{SS}	120	V _{SS}
27	V _{DD}	28	V _{DD}	69	**CS0	70	A12	121	DQ24	122	DQ56
29	A0	30	A3	71	**CS1	72	*A13	123	DQ25	124	DQ57
31	A1	32	A4	73	DU	74	**CLK1	125	DQ26	126	DQ58
33	A2	34	A5	75	V _{SS}	76	V _{SS}	127	DQ27	128	DQ59
35	V _{SS}	36	V _{SS}	77	NC	78	NC	129	V _{DD}	130	V _{DD}
37	DQ8	38	DQ40	79	NC	80	NC	131	DQ28	132	DQ60
39	DQ9	40	DQ41	81	V _{DD}	82	V _{DD}	133	DQ29	134	DQ61
41	DQ10	42	DQ42	83	DQ16	84	DQ48	135	DQ30	136	DQ62
43	DQ11	44	DQ43	85	DQ17	86	DQ49	137	DQ31	138	DQ63
45	V _{DD}	46	V _{DD}	87	DQ18	88	DQ50	139	V _{SS}	140	V _{SS}
47	DQ12	48	DQ44	89	DQ19	90	DQ51	141	SDA	142	SCL
49	DQ13	50	DQ45	91	V _{SS}	92	V _{SS}	143	V _{DD}	144	V _{DD}
				93	DQ20	94	DQ52				

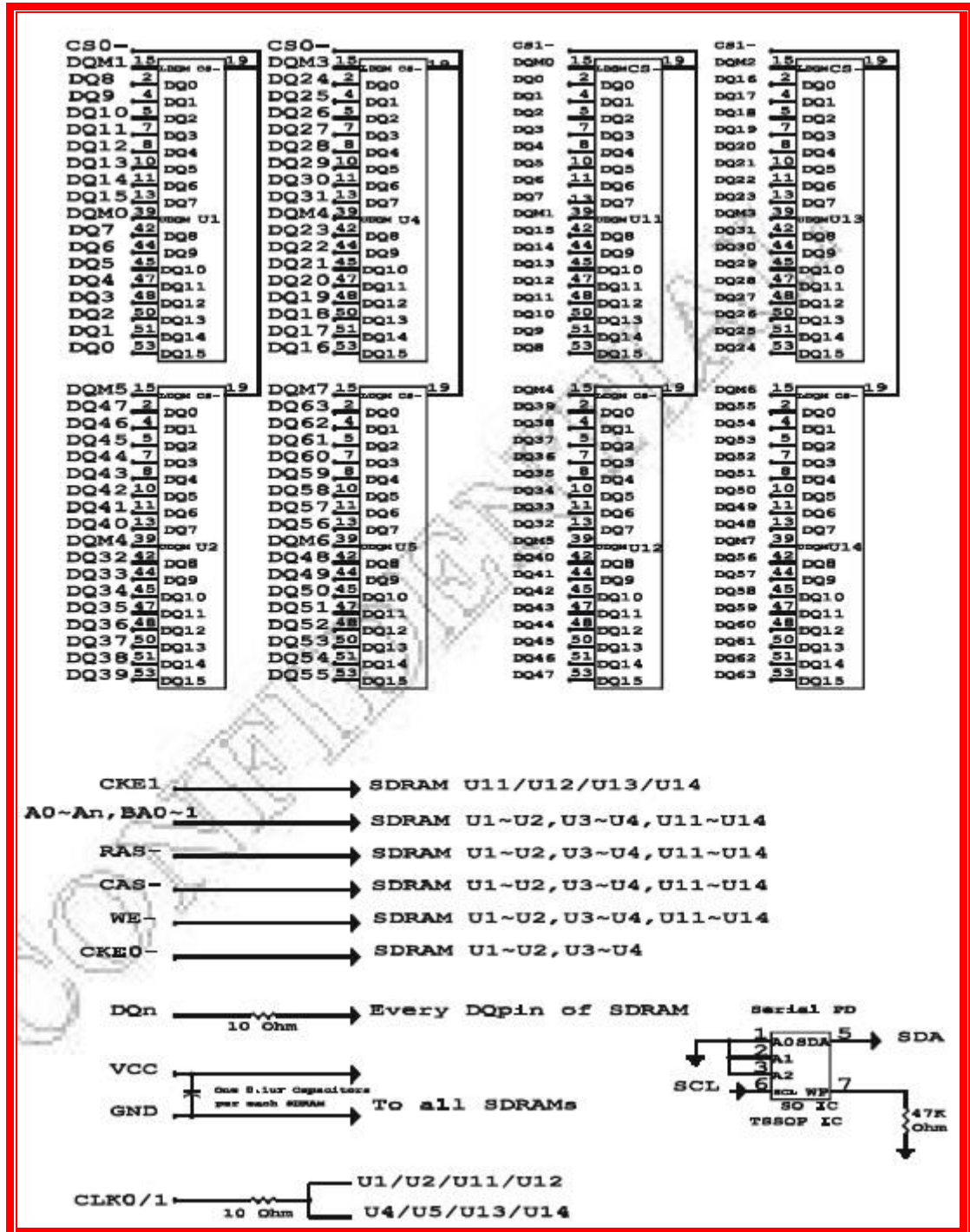
4. Architecture

Pin Definition

Pin Name	Description	Pin Name	Description
A0 - A12	SDRAM address bus	CKE0 – CKE1	SDRAM clock enable lines
SA0 - SA1	SDRAM Bank Address Inputs	SCL	Serial Presence Detect Clock Input
RAS-	SDRAM row address strobe	SDA	Serial Presence Detect Data input/output
CAS-	SDRAM column address strobe	DQM0 – DQM7	SDRAM data masks
WE-	SDRAM write enable	V _{DD}	Power Supply
CS0- - CS1-	Chip select input	GND	Ground
CLK0 – CLK1	SDRAM Clock input.	DU	Spare Pin
D0 – D63	DIMM memory data bus	NC	No connection

5. Function Block Diagram:

- (256MB, 1 Rank, 32Mx16 SDR SDRAMs)
- Front side U1, U2, U4, U5 used



6. Absolute Maximum Ratings

Symbol	Parameter	Rating	Units
T _{STG}	Storage Temperature	-55 to 150	°C
V _{INPUT}	Voltage input pins relative to Vss	-0.3 to +4.6	V
V _{DD}	Voltage on VDD supply relative to Vss	-0.3 to +4.6	V
V _{DDQ}	Voltage on VDDQ supply relative to Vss	-0.3 to +4.6	V

Note: Stresses greater than those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. This is stress rating only, and functional operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect reliability.

7. DC Operating Conditions

- DC Electrical Operating Conditions

($T_A = -0\text{ }^{\circ}\text{C} \sim 70\text{ }^{\circ}\text{C}$; $V_{SS} = 0\text{V}$)

Symbol	Parameter	Min	Typ.	Max	Units	Notes
VDD	Supply Voltage	3.0	3.3	3.6	V	1
VDDQ	Supply Voltage	3.0	3.3	3.6	V	1
V_{IH} (DC)	Input High (Logic1) Voltage	2.0	-	$V_{CC} + 0.3$	V	1,2
V_{IL} (DC)	Input Low (Logic0) Voltage	-0.5	-	0.8	V	1,3
Note: 1. All voltages referenced to Vss and VssQ 2. V_{IH} (max) = VDD + 1.2V for pulse width $\leq 5\text{ns}$. 3. V_{IL} (min) = VSS + -1.2V for pulse width $\leq 5\text{ns}$.						

- DC Electrical Characteristics

($T_A = 0\text{ }^{\circ}\text{C} \sim 70\text{ }^{\circ}\text{C}$; $V_{SS} = 0\text{V}$)

Symbol	Parameter	Min	Max	Units
I_{I(L)}	Input Leakage Current, any input ($0.0\text{V} \leq V_{IN} \leq V_{DD}$), All Other Pins Not Under Test = 0V	-2	2	μA
I_{O(L)}	Output Leakage Current (DOUT is disabled, $0.0\text{V} \leq V_{OUT} \leq V_{DDQ}$)	-2	2	μA
V_{OH}	Output Level (LVTTTL) Output "H" Level Voltage ($I_{OUT} = -2.0\text{mA}$)	2.4	-	V
V_{OL}	Output Level (LVTTTL) Output "L" Level Voltage ($I_{OUT} = +2.0\text{mA}$)	-	0.4	V

8. Capacitance

(at $T_A = 0\text{ }^{\circ}\text{C} \sim 25\text{ }^{\circ}\text{C}$; $V_{DD} = 3.3 \pm 0.3\text{V}$)

Symbol	Parameter	Min.	Max.	Units
C _{CLK}	Input Capacitance: CLK	4.5	6	pF
C _{IN}	Input Capacitance: All other input pins and balls	2.5	6	pF
C _{IO}	Input/Output Capacitance: DQ	4	6	pF

9. Operating, Standby, and Refresh Currents

- 256MB SODIMM (1 Rank, 32Mx16 SDR SDRAMs $T_A = 0\text{ }^{\circ}\text{C} \sim 70\text{ }^{\circ}\text{C}$; $V_{DDQ} = V_{DD} = 3.3\pm0.3\text{V}$)

Symbol	Parameter/Condition	PC-133	Unit
I _{CC1}	Operation Current: Burst length = 4, CL = 3, $t_{RC} > t_{RC}(\text{min})$, $t_{CK} > t_{CK}(\text{min})$, IO = 0 mA, 2 Bank Interleave Operation	740	mA
I _{CC2P}	Precharged Standby Current in Power Down Mode: $\text{CKE} < V_{IL}(\text{max})$, $t_{CK} > t_{CK}(\text{min})$	28	mA
I _{CC2N}	Precharged Standby Current in Non-Power Down Mode: $\text{CKE} > V_{IH}(\text{min})$, $t_{CK} > t_{CK}(\text{min})$, Input changed once in 3 cycles.	232	mA
I _{CC3N}	Active Standby Current in Non-Power Down Mode: $\text{CKE} > V_{IH}(\text{min})$, $t_{CK} > t_{CK}(\text{min})$, Input changed one time	300	mA
I _{CC3P}	Active Standby Current in Power Down Mode: $\text{CKE} < V_{IL}(\text{max})$, $t_{CK} > t_{CK}(\text{min})$	128	mA
I _{CC4}	Burst Operating Current: Burst length = Full Page, $t_{RC} = \text{Infinite}$, CL = 3, $t_{CK} > t_{CK}(\text{min})$, IO = 0 mA 2 Banks Activated	620	mA
I _{CC5}	Auto Refresh Current: $t_{RC} > t_{RC}(\text{min})$	1080	mA
I _{CC6}	Self Refresh Current: $\text{CKE} = < 0.2\text{ V}$	28	mA

- Currents given are valid for a single device. .
- These parameters depend on the cycle rate and are measured with the cycle determined by the minimum value of t_{CK} and t_{RC} .
Input signals are changed up to three times during $t_{RC}(\text{min})$.
- The specified values are obtained with the output open.
- Input signals are changed once during $t_{CK}(\text{min})$.
- Input signals are changed once during three clock cycles.
- Active Standby Current will be higher if Clock Suspend is entered during a burst read cycle (add 1mA per DQ).
- Input signals are stable.

10. AC Timing Specifications

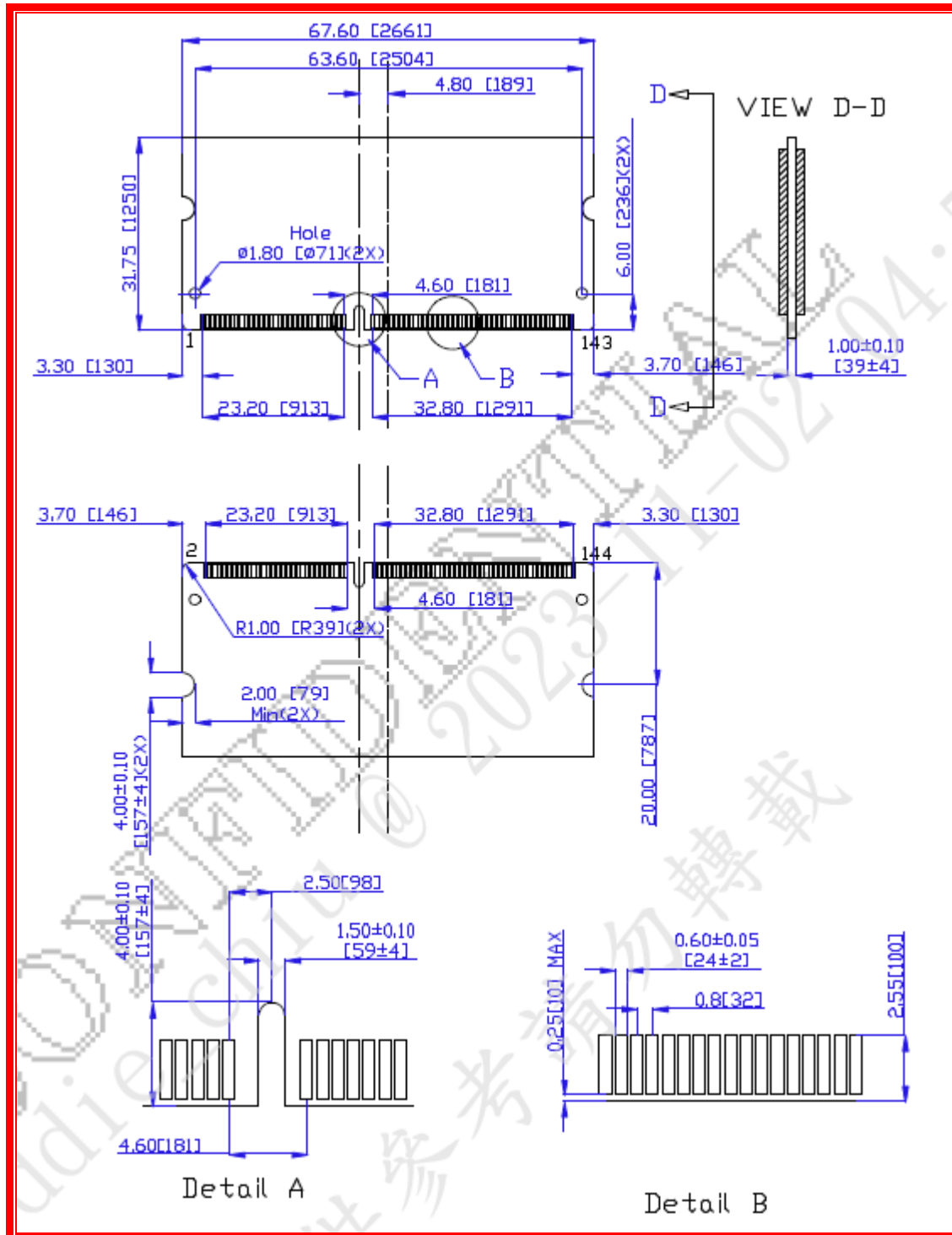
(T_A = 0 °C ~ 70 °C; V_{DDQ} = V_{DD} , See AC Characteristics)

Symbol	Parameter	PC-133		Unit
		Min.	Max.	
Clock and Clock Enable				
tAc	DQ output access time from CK/CK#	-	5.4	ns
tCH	CK high-level width	2.5	-	ns
tCL	CK low-level width	2.5	-	ns
fCK	System frequency	100	133	MHz
tCK	Clock Cycle Time	7.5	10	ns
tIS	input setup time	1.5	-	ns
tIH	input hold time	0.8	-	ns
tT	Transition time (rise and fall)	0.3	1.5-	ns
Command Parameters				
tRCD	/RAS to /CAS delay	15	-	ns
tRC	Cycle Time	65	-	ns
tRAS	Active command Period	45	100K	ns
tRP	Precharge Time	15	-	ns
tRRD	Bank to Bank delay time	15	-	ns
tCCD	/CAS to /CAS delay time (same bank)	1	-	CLK
Refresh Cycle				
tXSR	Self Refresh Exit to Active Time	1+ tRC	-	ns
tREF	Refresh Period (8192 cycles)	-	64	ms

Symbol	Parameter	PC-133		Unit
		Min.	Max.	
Read Cycle				
tOH	Data Out Hold Time	2.5	-	ns
tLZ	Data Out to Low Impedance Time	1	-	Ns
tHZ	Data Out to High Impedance Time	3	7	ns
tdQZ	DQM Data Out Disable Latency	-	2	CLK
Write Cycle				
tWR	Write Recovery Time for Auto precharge	2	-	CLK
tdQW	DQM Write Mask Latency	0	-	CLK

11. PACKAGE DIMENSION

- (256M, 1 Rank, 32Mx16 DDR SDRAMs)



Note: Device position is only for reference.

12. RoHS Declaration

innodisk	宜鼎國際股份有限公司 Innodisk Corporation	
Tel: (02) 7703-3000 Fax: (02) 7703-3555 Internet: http://www.innodisk.com/		
RoHS 自我宣告書 (RoHS Declaration of Conformity)		
Manufacturer Product: All Innodisk EM Flash and Dram products		
一、 宜鼎國際股份有限公司（以下稱本公司）特此保證售予貴公司之所有產品，皆符合歐盟 2011/65/EU 關於 RoHS 之規範要求。 Innodisk Corporation declares that all products sold to the company, are complied with European Union RoHS Directive (2011/65/EU) requirement		
二、 本公司同意因本保證書或與本保證書相關事宜有所爭議時，雙方宜友好協商，達成協議。 Innodisk Corporation agrees that both parties shall settle any dispute arising from or in connection with this Declaration of Conformity by friendly negotiations.		
Name of hazardous substance	Limited of RoHS ppm (mg/kg)	
Cd	< 100 ppm	
Pb	< 1000 ppm	
Hg	< 1000 ppm	
Chromium VI (Cr+6)	< 1000 ppm	
Polybromodiphenyl ether (PBDE)	< 1000 ppm	
Polybrominated Biphenyls (PBB)	< 1000 ppm	
立 保 證 書 人 (Guarantor)		
Company name 公司名稱： <u>Innodisk Corporation 宜鼎國際股份有限公司</u>		
Company Representative 公司代表人： <u>Richard Lee 李鐘亮</u>		
Company Representative Title 公司代表人職稱： <u>CEO 執行長</u>		
Date 日期： <u>2014 / 07 / 29</u>		
  <u>(Company Stamp/公司大小章)</u>		

Revision Log

Rev	Date	Modification
0.1	14 th April 2016	Preliminary Edition
1.0	14 th April 2016	Official Release.
1.1	2 nd November 2023	Updated 12. PACKAGE DIMENSION